

INITIAL PRODUCT/PROCESS CHANGE NOTIFICATION # 16790A

Generic Copy

Issue Date: 18-Jan-2012

<u>TITLE:</u> Initial PCN for transfer from the wafer fabs Gunma and Gifu in Japan to the Niigata waferfab.

PROPOSED FIRST SHIP DATE: starting 31 July 2012 until 30 June 2013 (the actual ship date will be different by each product, please check the responsible Sales person).

AFFECTED CHANGE CATEGORY(S): Wafer Fabrication Location Change

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office.

NOTIFICATION TYPE:

Initial Product/Process Change Notification (IPCN)

First change notification sent to customers. IPCNs are issued at least 120 days prior to implementation of the change. An IPCN is advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan.

The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN).

This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 90 days prior to implementation of the change.

DESCRIPTION AND PURPOSE:

This is an Initial Process Change Notification to announce the transfer of products from Sanyo wafer fabrication sites located in Gunma and Gifu Japan to the Niigata waferfab.

The product design and electrical specifications will remain identical. A full electrical characterization over the temperature range will be performed for each product to check the device functionality and electrical specifications. Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.

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QUALIFICATION PLAN:

Estimated Date for Qualification Completion: starting January 2012 till March 2012, dependent of the process/product.

Samples should be available after completion of Qualification.

Reliability Test Plan

Test Items	Test Condition
High Temperature Operating Life	Tj max, Vcc(VDD) opemax
Temperature Humidity Bias *	Ta=85degC, RH=85%, Vcc=Recommended
Temperature Humidity Storage *	Ta=85degC,RH=85%
Temperature Cycle *	Ta=-55degC 30min. <> Ta=150degC 30min.
High Temperature Storage	Ta=150degC
Electrostatic Discharge(MM)	Vcc pin versus each pin,Gnd pin versus each pin C=200pF, R=0 Ω

Note)

The test items with ${}^{m \star}$ mark are put into operation after the preconditioning(Reflow Soldering) .

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INITIAL PRODUCT/PROCESS CHANGE NOTIFICATION # 16790A List of affected Generic parts:

1410010-TRM-E	LB1638M-TLM-E
L79M05TLL-SONY-TL-E	LB1058W-1EW-E
L/9M051LL-SONY-IL-E	LB1041-E LB1830M-TLM-E
LA1140-E LA1145M-TLM-E	LB1850M-TEM-E
LA1145M-TLM-E	LB1836M-TLM-E
LA42032-E	LB1836M-VDO-TE-L
LA4537M-TE-L-E	LB1836M-VDO-TLM-E
LA4625-E	LB1837M-TLM-E
LA4631-E	LB1838M-MPB-E
LA4708N-E	LB1838M-TRM-E
LA47536-E	LB1843V-MPB-E
LA4809M-TLM-E	LB1843V-TLM-E
LA5735M-TLM-E	LB1846M-TLM-E
LA5744-HK-E	LB1847-E
LA5744MP-DL-E	LB1848M-TE-R-E
LA5771MP-DL-E	LB1848M-TLM-E
LA5774MP-DL-E	LB1848M-TRM-H
LA6242H-TE-L-E	LB1862M-TLM-E
LA6324NM-MPB-E	LB1909M-TE-L-E
LA6324NM-TLM-E	LB1930M-TLM-E
LA6500-E	LB1930M-TLM-H
LA6500L-A-SONY-FA-E	LB1935CL-TLM-E
LA6571-TLM-E	LB1936V-MPB-E
LA6581T-TE-L-E	LB1936V-TLM-E
LA6585T-TLM-E	LB1938T-TLM-E
LA6595T-TLM-E	LB1938T-TLM-H
LA78045-E	LB1941T-TLM-E
LA9520V-MPB-E	LB1945H-TLM-E
LA9520V-TLM-E	LB1946-E
LB11683H-MPB-E	LB1947-E
LB11683H-TLM-E	LB1948M-TE-L-E
LB11946-E	LB1962M-MPB-E
LB11948T-MPB-E	LB1962M-TLM-E
LB11948T-TLM-E	LB1973M-TLM-E
LB11983-E	LB8649W-MPB-E
LB1638-E	LB8649W-TBM-E

List of affected Customer specific parts:

ICC1-TLM-E	LB1836M-VDO-L-E
LA1837M-TLM-E	